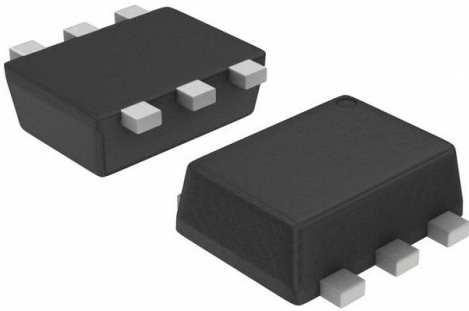


NTZS3151PT1H Datasheet

www.digi-electronics.com



DiGi Electronics Part Number	NTZS3151PT1H-DG
Manufacturer	onsemi
Manufacturer Product Number	NTZS3151PT1H
Description	MOSFET P-CH 20V 860MA SOT563-6
Detailed Description	P-Channel 20 V 860mA (Ta) 170mW (Ta) Surface Mount SOT-563

<https://www.DiGi-Electronics.com>



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

NTZS3151PT1H

Series:

-

FET Type:

P-Channel

Drain to Source Voltage (Vdss):

20 V

Drive Voltage (Max Rds On, Min Rds On):

1.8V, 4.5V

Vgs(th) (Max) @ Id:

1V @ 250μA

Vgs (Max):

±8V

FET Feature:

-

Operating Temperature:

-55°C ~ 150°C (Tj)

Supplier Device Package:

SOT-563

Base Product Number:

NTZS3151

Manufacturer:

onsemi

Product Status:

Obsolete

Technology:

MOSFET (Metal Oxide)

Current - Continuous Drain (Id) @ 25°C:

860mA (Ta)

Rds On (Max) @ Id, Vgs:

150mOhm @ 950mA, 4.5V

Gate Charge (Qg) (Max) @ Vgs:

5.6 nC @ 4.5 V

Input Capacitance (Ciss) (Max) @ Vds:

458 pF @ 16 V

Power Dissipation (Max):

170mW (Ta)

Mounting Type:

Surface Mount

Package / Case:

SOT-563, SOT-666

Environmental & Export classification

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

REACH Status:

REACH Unaffected

HTSUS:

8541.21.0095

NTZS3151P

MOSFET – P-Channel, Small Signal, SOT-563

-20 V, -950 mA

Features

- Low $R_{DS(on)}$ Improving System Efficiency
- Low Threshold Voltage
- Small Footprint 1.6 x 1.6 mm
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Load/Power Switches
- Battery Management
- Cell Phones, Digital Cameras, PDAs, Pagers, etc.

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted.)

Parameter	Symbol	Value	Unit	
Drain-to-Source Voltage	V_{DSS}	-20	V	
Gate-to-Source Voltage	V_{GS}	± 8.0	V	
Continuous Drain Current (Note 1)	Steady State	$T_A = 25^\circ\text{C}$	-860	mA
		$T_A = 70^\circ\text{C}$	-690	
Power Dissipation (Note 1)	Steady State	P_D	170	mW
Continuous Drain Current (Note 1)	$t \leq 5\text{ s}$	$T_A = 25^\circ\text{C}$	-950	mA
		$T_A = 70^\circ\text{C}$	-760	
Power Dissipation (Note 1)	$t \leq 5\text{ s}$	P_D	210	mW
Pulsed Drain Current	$t_p = 10\ \mu\text{s}$	I_{DM}	-4.0	A
Operating Junction and Storage Temperature	T_J, T_{STG}	-55 to 150		$^\circ\text{C}$
Source Current (Body Diode)	I_S	-360		mA
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)	T_L	260		$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

Parameter	Symbol	Max	Unit
Junction-to-Ambient – Steady State (Note 1)	$R_{\theta JA}$	720	$^\circ\text{C}/\text{W}$
Junction-to-Ambient – $t \leq 5\text{ s}$ (Note 1)	$R_{\theta JA}$	600	

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Surface-mounted on FR4 board using 1 in. sq. pad size (Cu. area = 1.127 in. sq. [1 oz.] including traces).

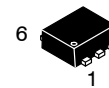
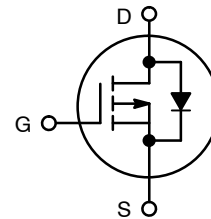


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<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(on)}$ Typ	I_D Max
-20 V	120 m Ω @ -4.5 V	-950 mA
	144 m Ω @ -2.5 V	
	195 m Ω @ -1.8 V	

P-Channel MOSFET



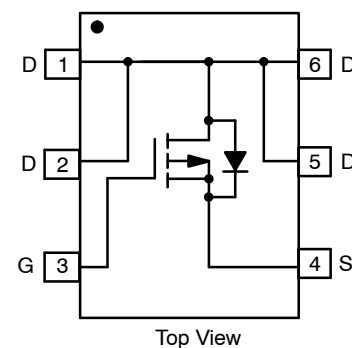
SOT-563-6
CASE 463A

MARKING DIAGRAM



TX = Specific Device Code
M = Date Code
▪ = Pb-Free Package
(Note: Microdot may be in either location)

PINOUT: SOT-563



ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 4 of this data sheet.

NTZS3151P**ELECTRICAL CHARACTERISTICS** ($T_J = 25^\circ\text{C}$ unless otherwise noted.)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$			-13		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	$V_{GS} = 0\text{ V}, T_J = 25^\circ\text{C}$			-1.0	μA
		$V_{DS} = -20\text{ V}, T_J = 125^\circ\text{C}$			-5.0	
Gate-to-Source Leakage Current	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8.0\text{ V}$			± 100	nA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage	$V_{GS(TH)}$	$V_{GS} = V_{DS}, I_D = -250\ \mu\text{A}$	-0.45		-1.0	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$			2.4		mV/°C
Drain-to-Source On Resistance	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -950\text{ mA}$		120	150	m Ω
		$V_{GS} = -4.5\text{ V}, I_D = -770\text{ mA}$		112	142	
		$V_{GS} = -2.5\text{ V}, I_D = -670\text{ mA}$		144	200	
		$V_{GS} = -1.8\text{ V}, I_D = -200\text{ mA}$		195	240	
Forward Transconductance	g_{FS}	$V_{DS} = -10\text{ V}, I_D = -810\text{ mA}$		3.1		S

CHARGES AND CAPACITANCES

Input Capacitance	C_{ISS}	$V_{GS} = 0\text{ V}, f = 1.0\text{ MHz}, V_{DS} = -16\text{ V}$		458		pF
Output Capacitance	C_{OSS}			61		
Reverse Transfer Capacitance	C_{RSS}			38		
Total Gate Charge	$Q_{G(TOT)}$	$V_{GS} = -4.5\text{ V}, V_{DS} = -10\text{ V}; I_D = -770\text{ mA}$		5.6		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.6		
Gate-to-Source Charge	Q_{GS}			0.9		
Gate-to-Drain Charge	Q_{GD}			1.2		

SWITCHING CHARACTERISTICS (Note 3)

Turn-On Delay Time	$t_{d(ON)}$	$V_{GS} = -4.5\text{ V}, V_{DD} = -10\text{ V}, I_D = -950\text{ mA}, R_G = 6.0\ \Omega$		5.0		ns
Rise Time	t_r			12		
Turn-Off Delay Time	$t_{d(OFF)}$			23.7		
Fall Time	t_f			18		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V_{SD}	$V_{GS} = 0\text{ V}, I_S = -360\text{ mA}$	$T_J = 25^\circ\text{C}$	-0.64	-0.9	V
			$T_J = 125^\circ\text{C}$	-0.5		
Reverse Recovery Time	t_{RR}	$V_{GS} = 0\text{ V}, di_S/dt = 100\text{ A}/\mu\text{s}, I_S = -360\text{ mA}$		10.5		ns

- Pulse Test: pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
- Switching characteristics are independent of operating junction temperatures.

NTZS3151P

TYPICAL PERFORMANCE CURVES ($T_J = 25^\circ\text{C}$ unless otherwise noted)

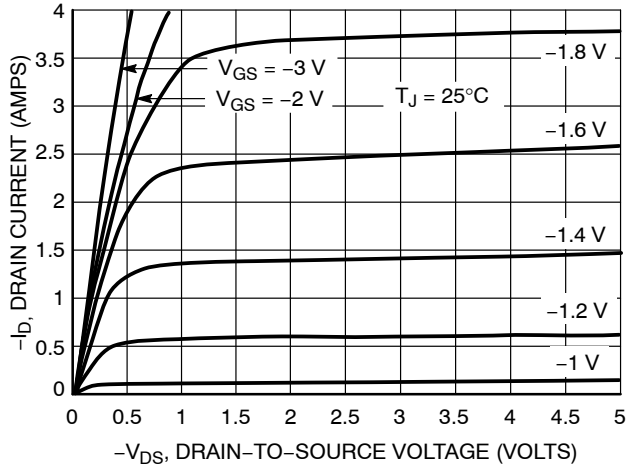


Figure 1. On-Region Characteristics

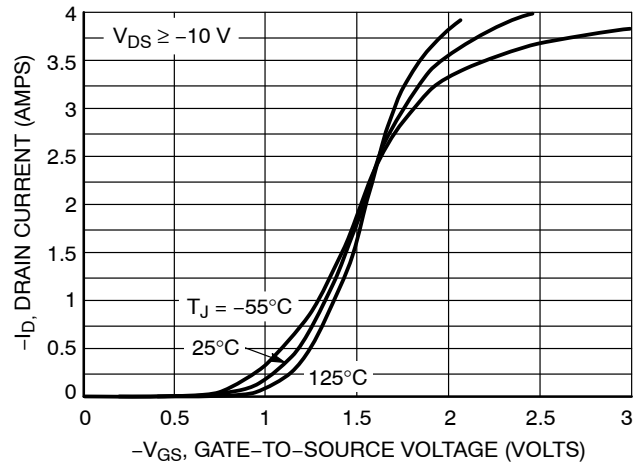


Figure 2. Transfer Characteristics

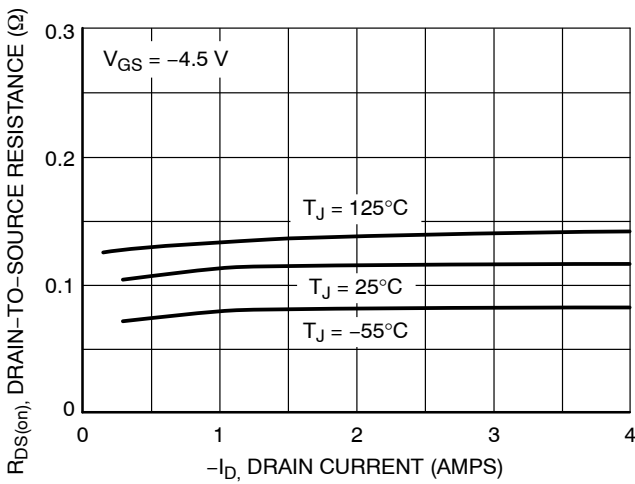


Figure 3. On-Resistance vs. Drain Current and Temperature

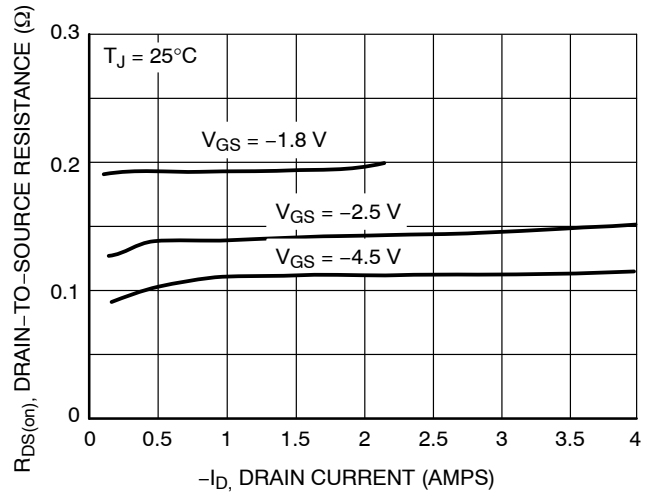


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

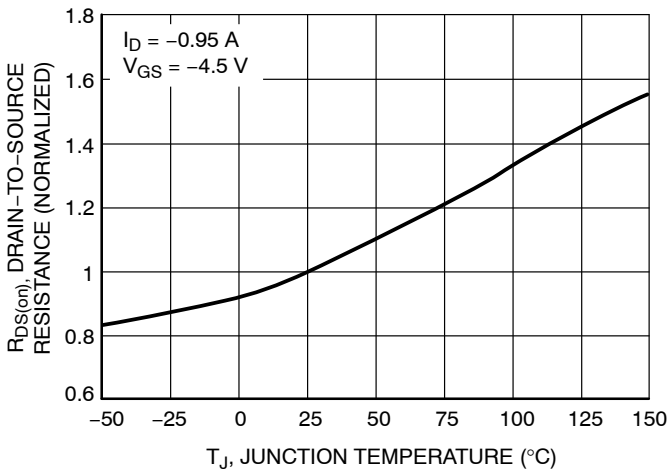


Figure 5. On-Resistance Variation with Temperature

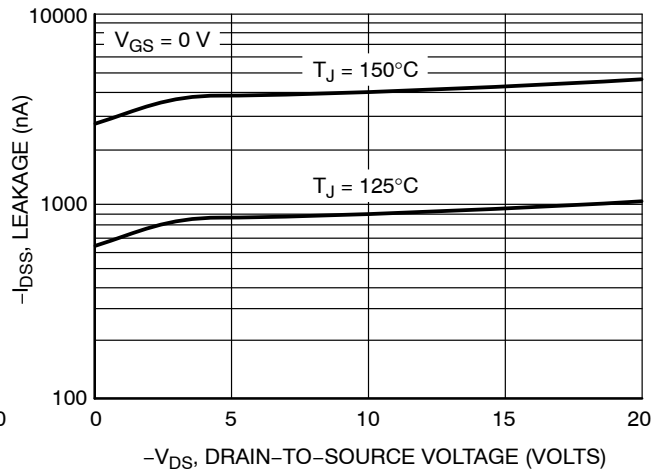


Figure 6. Drain-to-Source Leakage Current vs. Voltage

NTZS3151P

TYPICAL PERFORMANCE CURVES (T_J = 25°C unless otherwise noted)

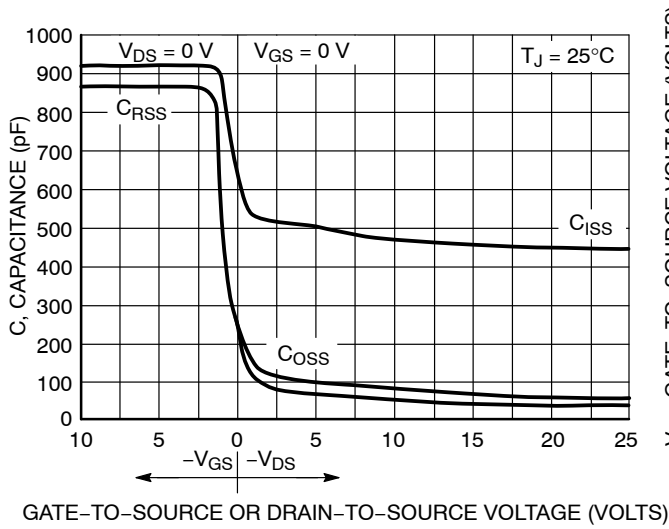


Figure 7. Capacitance Variation

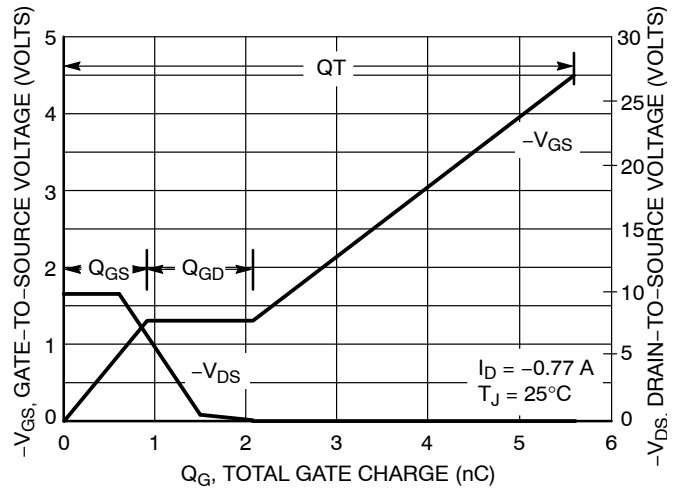


Figure 8. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

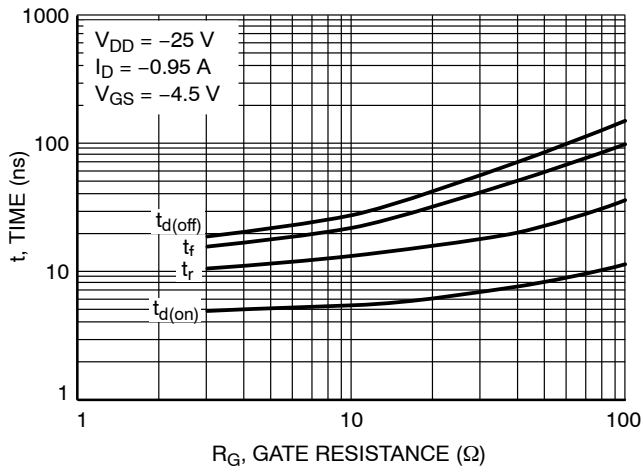


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

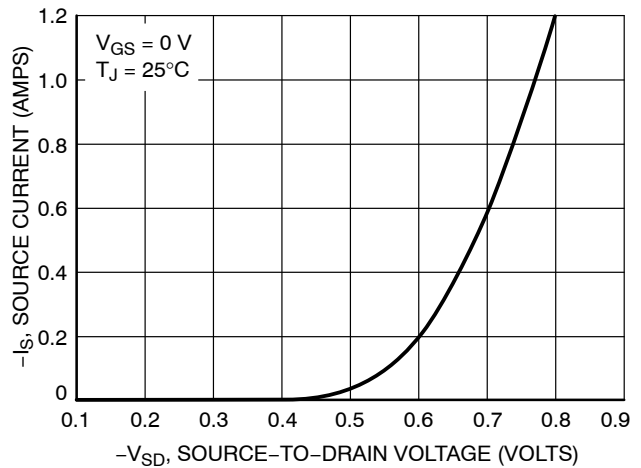


Figure 10. Diode Forward Voltage vs. Current

ORDERING INFORMATION

Device	Package	Shipping
NTZS3151PT1G	SOT-563 (Pb-Free)	4000 / Tape & Reel
NTZS3151PT1H	SOT-563 (Pb-Free)	4000 / Tape & Reel
NTZS3151PT5G	SOT-563 (Pb-Free)	8000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



**MECHANICAL CASE OUTLINE
PACKAGE DIMENSIONS**

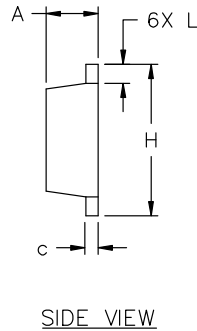
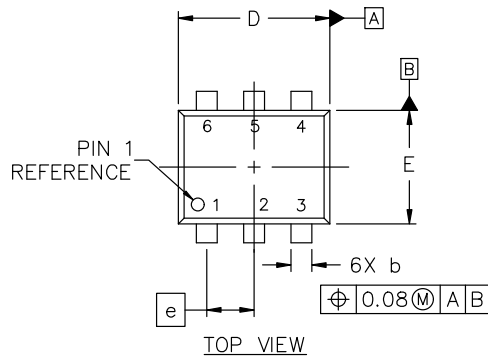


SOT-563-6 1.60x1.20x0.55, 0.50P
CASE 463A
ISSUE J

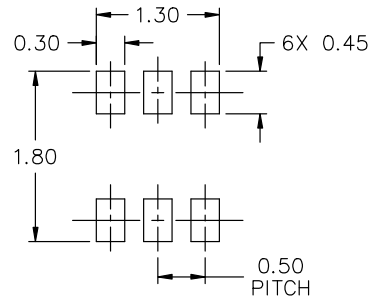
DATE 15 FEB 2024

NOTES:

1. DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
2. ALL DIMENSION ARE IN MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.



DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.50	0.55	0.60
b	0.17	0.22	0.27
c	0.08	0.13	0.18
D	1.50	1.60	1.70
E	1.10	1.20	1.30
e	0.50 BSC		
H	1.50	1.60	1.70
L	0.10	0.20	0.30



- | | | |
|---|---|---|
| STYLE 1:
PIN 1. EMITTER 1
2. BASE 1
3. COLLECTOR 2
4. EMITTER 2
5. BASE 2
6. COLLECTOR 1 | STYLE 2:
PIN 1. EMITTER 1
2. EMITTER 2
3. BASE 2
4. COLLECTOR 2
5. BASE 1
6. COLLECTOR 1 | STYLE 3:
PIN 1. CATHODE 1
2. CATHODE 1
3. ANODE/ANODE 2
4. CATHODE 2
5. CATHODE 2
6. ANODE/ANODE 1 |
|---|---|---|

- | | | |
|--|---|---|
| STYLE 4:
PIN 1. COLLECTOR
2. COLLECTOR
3. BASE
4. EMITTER
5. COLLECTOR
6. COLLECTOR | STYLE 5:
PIN 1. CATHODE
2. CATHODE
3. ANODE
4. ANODE
5. CATHODE
6. CATHODE | STYLE 6:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. CATHODE
6. CATHODE |
|--|---|---|

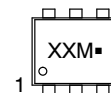
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|---|---|---|
| STYLE 7:
PIN 1. CATHODE
2. ANODE
3. CATHODE
4. CATHODE
5. ANODE
6. CATHODE | STYLE 8:
PIN 1. DRAIN
2. DRAIN
3. GATE
4. SOURCE
5. DRAIN
6. DRAIN | STYLE 9:
PIN 1. SOURCE 1
2. GATE 1
3. DRAIN 2
4. SOURCE 2
5. GATE 2
6. DRAIN 1 |
|---|---|---|

- | | |
|--|--|
| STYLE 10:
PIN 1. CATHODE 1
2. N/C
3. CATHODE 2
4. ANODE 2
5. N/C
6. ANODE 1 | STYLE 11:
PIN 1. EMITTER 2
2. BASE 2
3. COLLECTOR 1
4. EMITTER 1
5. BASE 1
6. COLLECTOR 2 |
|--|--|

RECOMMENDED MOUNTING FOOTPRINT*

* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERM/D.

GENERIC MARKING DIAGRAM*



XX = Specific Device Code
M = Month Code
▪ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION:	SOT-563-6 1.60x1.20x0.55, 0.50P	PAGE 1 OF 1

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OUR CERTIFICATE

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